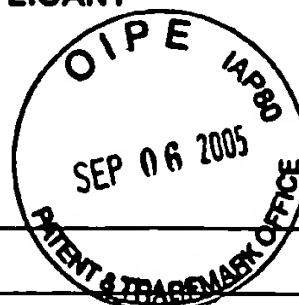


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**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(Use as many sheets as necessary)



Complete if Known

Application Number	09/945,507
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2824
Examiner Name	Dinh, Son

Sheet 1 of 2

Attorney Docket No: 1303.014US1

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	Application Number	09/945,507
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	Group Art Unit	2824
	Examiner Name	Dinh, Son
Sheet 2 of 2	Attorney Docket No: 1303.014US1	

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